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Serial No.: To Be Assigned

LIST OF DOCUMENTS CITED BY APPLICANT
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Applicants:

Kevin J. Linthicum, et al.

Filing Date:

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U.S. PATENT DOCUMENTS

Examiner Initials		Document No.	Date	Name	Class	Subclass	Filing Date if Appropriate
gm	1	Re. 34,861	02/14/95	Davis et al.	437	100	
	2	6,153,010	11/28/00	Koyoku et al.	117	95	
	3	6,100,111	08/08/00	Konstantinov	438	92	
	4	6,100,104	08/08/00	Haerle	438	33	
	5	6,051,849	04/08/00	Davis	257	103	
	6	6,051,849	04/08/00	Davis	257	103	
	7	5,915,194	06/22/99	Powell et al.	438	478	
	8	5,912,477	06/15/99	Negley	257	95	
	9	5,880,485	03/09/99	Marx et al.	257	94	
	10	5,877,070	03/02/99	Goesele et al.	438	458	
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	14	5,760,426	06/02/98	Marx et al.	257	190	
	15	5,710,057	01/20/98	Kenney	437	62	
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	21	4,946,547	08/09/90	Palmour et al.	156	643	
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	37	11-145516	05/28/99	Japan			X (Abstract)
	38	WO 98/47170	10/22/98	PCT			
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	41	JP 9-324997	11/26/97	Japan			X
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	43	JP 9-277448	10/09/97	Japan			X
	44	JP 9-201477	07/28/97	Japan			X
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	46	JP 9-174494	06/30/97	Japan			X
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	49	JP 8-153931	06/11/96	Japan			X (Abstract)
gm	50	JP 8-125251	05/17/96	Japan			X (Abstract)

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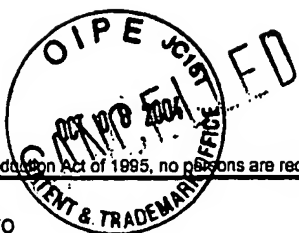
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary) Sheet 1 of 1		Complete If Known	
		Application Number	10/633,952
		Filing Date	August 4, 2003
		First Named Inventor	Linthicum, Kevin J.
		Art Unit	2815
		Examiner Name	Jerome Jackson, Jr.
		Attorney Docket Number	013921-000025

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Examiner Initials ¹	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)				
GA	AA	5,633,192		05-27-97	Moustakas et al.	
	AB	5,686,738		11-11-97	Moustakas	
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GA	AF	Lahreche et al., "Growth of High Quality GaN by low pressure metal-organic vapour phase epitaxy (LP_MOVEPE) from 3D Islands and lateral overgrowth," <u>Journal of Crystal Growth</u> , 205 (1999) 245-252	
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Examiner Signature	<i>G. Jackson</i>	Date Considered	11/5/04
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